

DS12W THRU DS120W

DESCRIPTION

Cathode

Anode

Surface Mount Schottky Barrier Rectifier Reverse Voltage - 20 to 200 V Forward Current - 1.0 A FEATURES

- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- Metal silicon junction, majority carrier conduction

MECHANICAL DATA

- · Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight:15mg 0.00048oz

Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 $^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 $^{\circ}$ C

		14
1	2	-
Top View		
Marking Code:	DS12W	S12
out a color sine a co lo constal design de	DS14W	S14
	DS16W	S16
	DS18W	S18
	DS110W	S110
	DS112W	S112
	DS115W	S115
	DS120W	S120

PINNING

PIN

2

Parameter	Symbols	DS12W	DS14W	DS16W	DS18W	DS110W	DS112W	D8115W	DS120W	Unita
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I _{F(AV)}	1.0						А		
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}		40 30				30		А	
Max Instantaneous Forward Voltage at 1 A	V _F	0.55		0.70		0.85		0.90		V
Maximum DC Reverse Current T _a = 25°C at Rated DC Reverse Voltage T _a = 100°C	I _R		0.3 0.2 10 5					0.1		mA
Typical Junction Capacitance 13	C;	110		80					рF	
Typical Thermal Resistance ²⁾	R _{gJA}	115						°C/W		
Operating Junction Temperature Range	Тј	-55 ~ +125						°C		
Storage Temperature Range	T _{s1g}	-55 ~ +150					°C			

¹⁾ Measured at 1MHz and applied reverse voltage of 4 V D.C.

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²⁾ P.C.B. mounted with 0.2 X 0.2" (5 X 5 mm) copper pad areas.



DS12W THRU DS120W

Fig.1 Forward Current Derating Curve

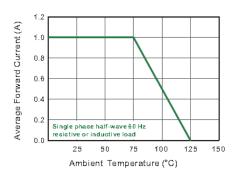


Fig.3 Typical Forward Characteristic

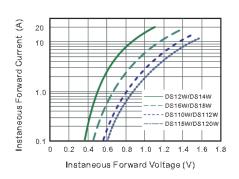


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

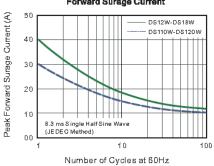


Fig.2 Typical Reverse Characteristics

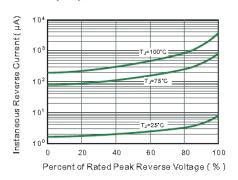


Fig.4 Typical Junction Capacitance

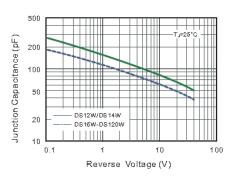
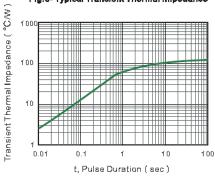


Fig.6- Typical Transient Thermal Impedance



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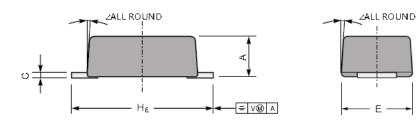


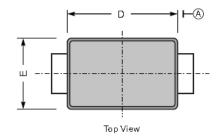
DS12W THRU DS120W

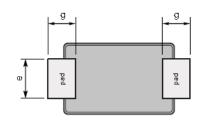
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123FL



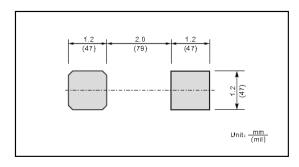




Bottom View

UNIT Α С D Е е Hε _ g 0.20 0.9 1.1 2.9 1.9 1.1 3.8 max mm 3.5 min 0.9 0.12 2.6 1.7 0.8 0.7 7° max 43 7.9 114 75 43 35 150 mil min 35 4.7 102 67 31 28 138

The recommended mounting pad size



Marking

Type number	Marking code			
DS12W	S12			
DS14W	S14			
DS16W	S16			
DS18W	S18			
DS110W	S110			
DS112W	S112			
DS115W	S115			
DS120W	S120			

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